

1N5400 THRU 1N5408 3.0AMP. Standard Silicon Rectifiers

VOLTAGE:50 TO 1000V

CURRENT:3.0A



Specification Features:

- Case: Epoxy, Molded
- Weight: 1.20Gram (Approximately)
- High current capability, Low leakage current
- High surge current capability
- Finish: All External Surfaces Corrosion Resistant And Terminal Leads Are Readily Solderable
- Lead And Mounting Surface Temperature For Soldering Purposed:
260°C Max. For 10 Seconds 1/16 Inch From Case
- RoHS Compliant
Cathode Indicated By Polarity Band

DEVICE MARKING DIAGRAM



1N54XX : Device Name 1N5400-1N5408
KEL : KEL Logo

Absolute Maximum Ratings $T_A = 25^\circ\text{C}$ unless otherwise noted

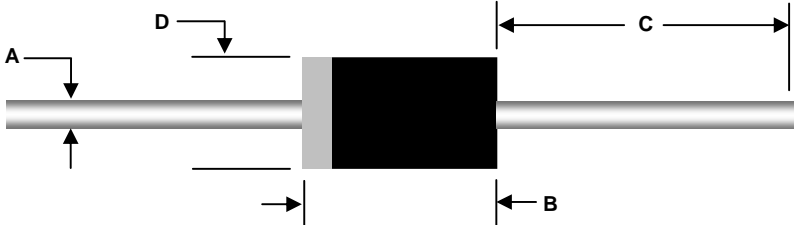
Parameter	Symbol	1N 5400	1N 5401	1N 5402	1N 5404	1N 5406	1N 5407	1N 5408	Units
Maximum Repetitive Peak Reverse Voltage	V_{RRM}	50	100	200	400	600	800	1000	V
Maximum DC Blocking Voltage	V_R	50	100	200	400	600	800	1000	V
Maximum Average Forward Rectifier Current. (0.375" Lead Length @ $T_A=75^\circ\text{C}$)	$I_{F(AV)}$	3.0							A
Non-repetitive Peak Forward Surge Current. (8.3mS Single Half Sine-wave)	I_{FSM}	200							A
Operating Junction and Storage Temperature Range	T_J, T_{STG}	-65 to +150							$^\circ\text{C}$
Thermal Resistance (Note 1) (Junction to Ambient)	$R_{\theta JA}$	20							$^\circ\text{C/W}$

Electrical Characteristics $T_A = 25^\circ\text{C}$ unless otherwise noted

Parameter	Symbol	1N 5400	1N 5401	1N 5402	1N 5404	1N 5406	1N 5407	1N 5408	Units
Reverse Current @ V_R	I_R	5							μA
Forward Voltage @3A	V_F	1.1							V
Total Capacitance (Note 2) @ $V_R=4\text{V}, f=1\text{MHz}$	C_T	50							pF

NOTE: (1) Thermal resistance from junction to ambient at 0.375" lead length, vertical P.C. board mounted
(2) Measured at 1 MHz and applied reverse voltage of 4.0V D.C.

Package Outline

Package	Case Outline				
DO-201AD					
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	DIM	Millimeters		Inches	
		Min	Max	Min	Max
	A	1.19	1.30	0.046	0.052
	B	7.20	9.60	0.285	0.375
C	25.40	---	1.000	---	
D	4.80	5.30	0.190	0.210	